In the Claims:

Please enter the following amended claims 1 and 14:

1. (Once Amended) A circuit comprising:

a bipolar transistor having a base, an emitter, and a collector, said bipolar transistor comprising a SiGe HBT;

a field effect transistor having a gate, a source, and a drain;

said base of said bipolar transistor being an input of said circuit;

said emitter of said bipolar transistor being coupled to a first reference voltage;

said collector of said bipolar transistor being coupled to said source of said field effect transistor;

said gate of said field effect transistor being coupled to a bias voltage;

said drain of said field effect transistor being coupled to a second reference voltage;

said drain of said field effect transistor being an output of said circuit, and

wherein said drain of said field effect transistor is not coupled to said base of said bipolar transistor by a feedback network.

14. (Once Amended) A BiFET low noise amplifier comprising:

a bipolar transistor having a base, an emitter, and a collector, said bipolar transistor comprising a SiGe HBT;

a field effect transistor having a gate, a source, and a drain;

an input of said BiFET low noise amplifier being coupled to said base of said bipolar transistor;

said emitter of said bipolar transistor being coupled to a first reference voltage through a first impedance circuit;

said collector of said bipolar transistor being coupled to said source of said field effect transistor;

said gate of said field effect transistor being coupled to a bias voltage;

said drain of said field effect transistor being coupled to a second reference voltage through a second impedance circuit, said drain of said field effect transistor being coupled to an output of said BiFET low noise amplifier, and wherein said drain of said field effect transistor is not coupled to said base of said bipolar transistor by a feedback network.